Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-43. (Canceled)

44. (Previously Presented) A thin film transistor including a plurality of component parts comprising:

a channel region;

a gate electrode opposed to the channel region;

a gate insulating film provided between the channel region and the gate electrode;

a source-drain region connected to said channel region;

a source-drain wiring layer electrically connected to said source-drain region;

a gate wiring layer electrically connected to said gate electrode,

wherein at least one of the source-drain region and the gate electrode comprises an extension over which a plurality of contact holes are formed.

45-46. (Canceled)

47. (Previously Presented) A thin film transistor including a plurality of component parts comprising:

a channel region;

a gate electrode opposed to the channel region;

a gate insulating film provided between the channel region and the gate electrode;

a source-drain region connected to said channel region;

a source-drain wiring layer electrically connected to said source-drain region; and

a gate wiring layer electrically connected to said gate electrode,

at least one of the component parts being formed from a conductive film or a semiconductor film and being provided with a radiating extension extending outwardly from the at least one component part, said radiating extension extending outwardly from both sides of said gate electrode and is provided on at least one end of said gate electrode; and

wherein said gate wiring layer is electrically connected to the radiating extension of said gate electrode by a plurality of contact holes.

48. (Previously Presented) A thin film transistor including a plurality of component parts comprising:

a channel region;

a gate electrode opposed to the channel region;

a gate insulating film provided between the channel region and the gate electrode;

a source-drain region connected to said channel region;

a source-drain wiring layer electrically connected to said source-drain region; and

a gate wiring layer electrically connected to said gate electrode,

at least one of the component parts being formed from a conductive film or a semiconductor film and being provided with a radiating extension extending outwardly from the at least one component part, said radiating extension extending from both sides of said channel region; and

said radiating extension extending from both sides of said source-drain region and said source-drain wiring layer is electrically connected to the radiating extension of said source-drain region by a plurality of contact holes.

49. (Previously Presented) A thin film transistor including a plurality of component parts comprising:

a channel region;

a gate electrode opposed to the channel region;

a gate insulating film provided between the channel region and the gate electrode;

a source-drain region connected to said channel region;

a source-drain wiring layer electrically connected to said source-drain region; and

a gate wiring layer electrically connected to said gate electrode,

at least one of the component parts being formed from a conductive film or a semiconductor film and being provided with a radiating extension extending outwardly from the at least one component part, said radiating extension extending from both sides of said source-drain region and wherein said source-drain wiring layer electrically connected to the radiating extension of said source-drain region by a plurality of contact holes.

50. (Currently Amended) A CMOS inverter circuit, comprising:

two thin film transistors having an inverse conductivity type from each other, each thin film transistor including a plurality of component parts that include:

a channel region;

a gate electrode opposed to the channel region;

a gate insulating film provided between the channel region and the gate electrode;

a source-drain region connected to said channel region;

a source-drain wiring layer electrically connected to said source-drain region; and

a gate wiring layer electrically connected to said gate electrode,

at least one of the component parts being formed from a conductive film or a semiconductor film and being provided with a radiating extension extending outwardly from the at least one component part, said radiating extension extending from both sides of said source-drain region, ~~said thin film transistors having an inverse conductivity type from each other,~~ adjacent identical-conductive-type source-drain regions of ~~said~~ adjacent thin film transistors having the same conductivity type being connected by respective said radiating extension.

51. (Currently Amended) A CMOS inverter circuit, comprising:

two thin film transistors having an inverse conductivity type from each other, each thin film transistor including a plurality of component parts that include:

a channel region;

a gate electrode opposed to the channel region;

a gate insulating film provided between the channel region and the gate electrode;

a source-drain region connected to said channel region;

a source-drain wiring layer electrically connected to said source-drain region; and

a gate wiring layer electrically connected to said gate electrode,

at least one of the component parts being formed from a conductive film or a semiconductor film and being provided with a radiating extension extending outwardly from the at least one component part, wherein said radiating extension extends from both sides of said source-drain region, ~~said thin film transistors having an inverse conductivity type from each other,~~ adjacent identical-conductive-type source-drain regions of ~~said~~ adjacent thin film

transistors having the same conductivity type being connected by respective said radiating extension,

wherein said radiating extension is provided with a conductivity by using an impurity identical to an impurity of said source-drain region to which said radiating extension is connected.

52. (Currently Amended) A CMOS inverter circuit, comprising:

two thin film transistors having an inverse conductivity type from each other, each thin film transistor including a plurality of component parts that include:

a channel region;

a gate electrode opposed to the channel region;

a gate insulating film provided between the channel region and the gate electrode;

a source-drain region connected to said channel region;

a source-drain wiring layer electrically connected to said source-drain region; and

a gate wiring layer electrically connected to said gate electrode,

at least one of the component parts being formed from a conductive film or a semiconductor film and being provided with a radiating extension extending outwardly from the at least one component part, said radiating extension extends from both sides of said source-drain region, ~~said thin film transistors having an inverse conductivity type from each other,~~ adjacent identical-conductive-type source-drain regions of ~~said~~ adjacent thin film transistors having the same conductivity type being connected by respective said radiating extension;

wherein said radiating extension is formed in a region opposed to said source-drain wiring layer, said source-drain wiring layer connecting the adjacent source-drain regions of ~~said~~ adjacent thin film transistors having the same conductivity type.

53. (Currently Amended) A liquid crystal display device comprising:

an active matrix substrate;

a driving circuit formed on the active matrix substrate and including a CMOS inverter circuit having two thin film transistors having an inverse conductivity type from each other, each thin film transistor including a plurality of component parts that include~~, the liquid crystal display device includes~~:

a channel region;

a gate electrode opposed to the channel region;

a gate insulating film provided between the channel region and the gate electrode;

a source-drain region connected to said channel region;

a source-drain wiring layer electrically connected to said source-drain region; and

a gate wiring layer electrically connected to said gate electrode,

at least one of the component parts being formed from a conductive film or a semiconductor film and being provided with a radiating extension extending outwardly from the at least one component part, wherein said radiating extension extends from both sides of said source-drain region, ~~said thin film transistors having an inverse conductivity type from each other,~~ adjacent identical-conductive-type source-drain regions of ~~said~~ adjacent thin film transistors having the same conductivity type being connected by respective said radiating extension~~;~~

~~forming a liquid crystal display device comprising an active matrix substrate on which a driving circuit including a CMOS inverter~~.

54. (Currently Amended) An electronic apparatus comprising a CMOS inverter circuit, the CMOS inverter circuit having two thin film transistors having an inverse conductivity type from each other, each thin film transistor including a plurality of component parts that include~~includes~~:

a channel region;

a gate electrode opposed to the channel region;

a gate insulating film provided between the channel region and the gate electrode;

a source-drain region connected to said channel region;

a source-drain wiring layer electrically connected to said source-drain region; and

a gate wiring layer electrically connected to said gate electrode,

at least one of the component parts being formed from a conductive film or a semiconductor film and being provided with a radiating extension extending outwardly from the at least one component part, wherein said radiating extension extends from both sides of said source-drain region, ~~said thin film transistors having an inverse conductivity type from each other,~~ adjacent identical-conductive-type source-drain regions of ~~said~~ adjacent thin film transistors having the same conductivity type being connected by respective said radiating extension~~;~~

~~an electronic apparatus comprising a CMOS inverter circuit~~.

55. (Currently Amended) A liquid crystal display device comprising:

an active matrix substrate;

a driving circuit formed on the active matrix substrate and including a CMOS inverter circuit having two thin film transistors having an inverse conductivity type from each other, each thin film transistor including a plurality of component parts that include~~, the liquid crystal display device includes~~:

a channel region;

a gate electrode opposed to the channel region;

a gate insulating film provided between the channel region and the gate electrode;

a source-drain region connected to said channel region;

a source-drain wiring layer electrically connected to said source-drain region; and

a gate wiring layer electrically connected to said gate electrode,

at least one of the component parts being formed from a conductive film or a semiconductor film and being provided with a radiating extension extending outwardly from the at least one component part, wherein said radiating extension extends from both sides of said source-drain region, ~~said thin film transistors having an inverse conductivity type from each other,~~ adjacent identical-conductive-type source-drain regions of ~~said~~ adjacent thin film transistors having the same conductivity type being connected by respective said radiating extension;

~~forming a liquid crystal display device comprising an active matrix substrate on which a driving circuit including a CMOS inverter;~~

said plurality of component parts each extending in a longitudinal direction, the radiating extension extending in a direction substantially perpendicular to the longitudinal direction.

56. (Currently Amended) An electronic apparatus comprising a CMOS inverter circuit, the CMOS inverter circuit having two thin film transistors having an inverse conductivity type from each other, each thin film transistor including a plurality of component parts that include~~includes~~:

a channel region;

a gate electrode opposed to the channel region;

a gate insulating film provided between the channel region and the gate electrode;

a source-drain region connected to said channel region;

a source-drain wiring layer electrically connected to said source-drain region; and

a gate wiring layer electrically connected to said gate electrode,

at least one of the component parts being formed from a conductive film or a semiconductor film and being provided with a radiating extension extending outwardly from the at least one component part, wherein said radiating extension extends from both sides of said source-drain region, ~~said thin film transistors having an inverse conductivity type from each other,~~ adjacent identical-conductive-type source-drain regions of ~~said~~ adjacent thin film transistors having the same conductivity type being connected by respective said radiating extension~~;~~

~~an electronic apparatus comprising a CMOS inverter circuit;~~

said plurality of component parts each extending in a longitudinal direction, the radiating extension extending in a direction substantially perpendicular to the longitudinal direction.

57-58. (Canceled)

59. (Previously Presented) An active matrix substrate including a driving circuit comprising a thin film transistor according to claim 44.

60. (Previously Presented) A circuit comprising:

at least two thin film transistors;

a wiring layer connected between a first source or drain region of a first thin film transistor and a second source or drain region of a second thin film transistor;

the wiring layer having an extension extending from both sides of the wiring layer along a substantially perpendicular direction to the direction of a line connected between the first source or drain region and the second source or drain region.

61. (Canceled)

62. (Previously Presented) A display device comprising a circuit according to Claim 60.

63. (Previously Presented) A liquid crystal display device comprising a circuit according to Claim 60.